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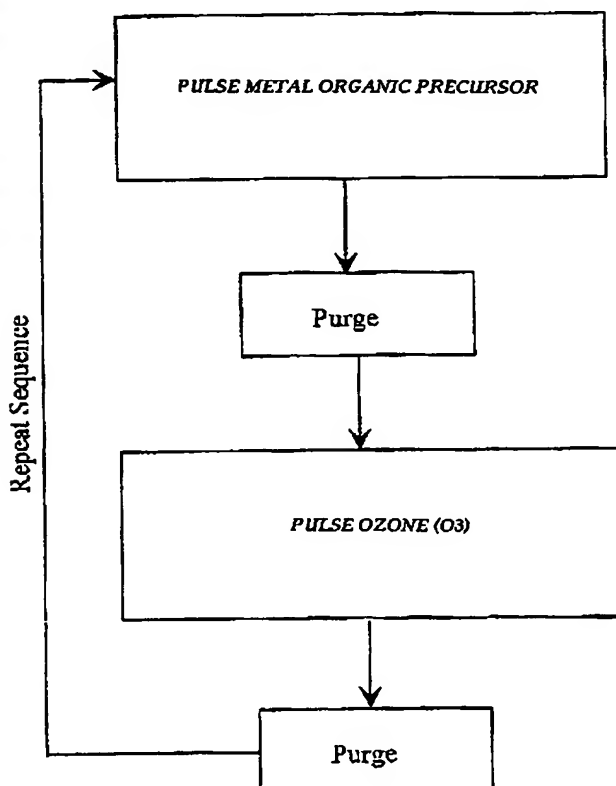
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(54) Title: ATOMIC LAYER DEPOSITION OF HIGH K METAL OXIDES



(57) Abstract: The present invention relates to the atomic layer deposition ("ALD") of high k dielectric layers of metal oxides containing Group 4 metals, including hafnium oxide, zirconium oxide, and titanium oxide. More particularly, the present invention relates to the ALD formation of Group 4 metal oxide films using an metal alkyl amide as a metal organic precursor and ozone as a co-reactant.



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